

UNIVERSITY OF TWENTE.

Local Conduction in Transition Metal Dichalcogenides: The Role of Stacking Faults, Defects and Alloying

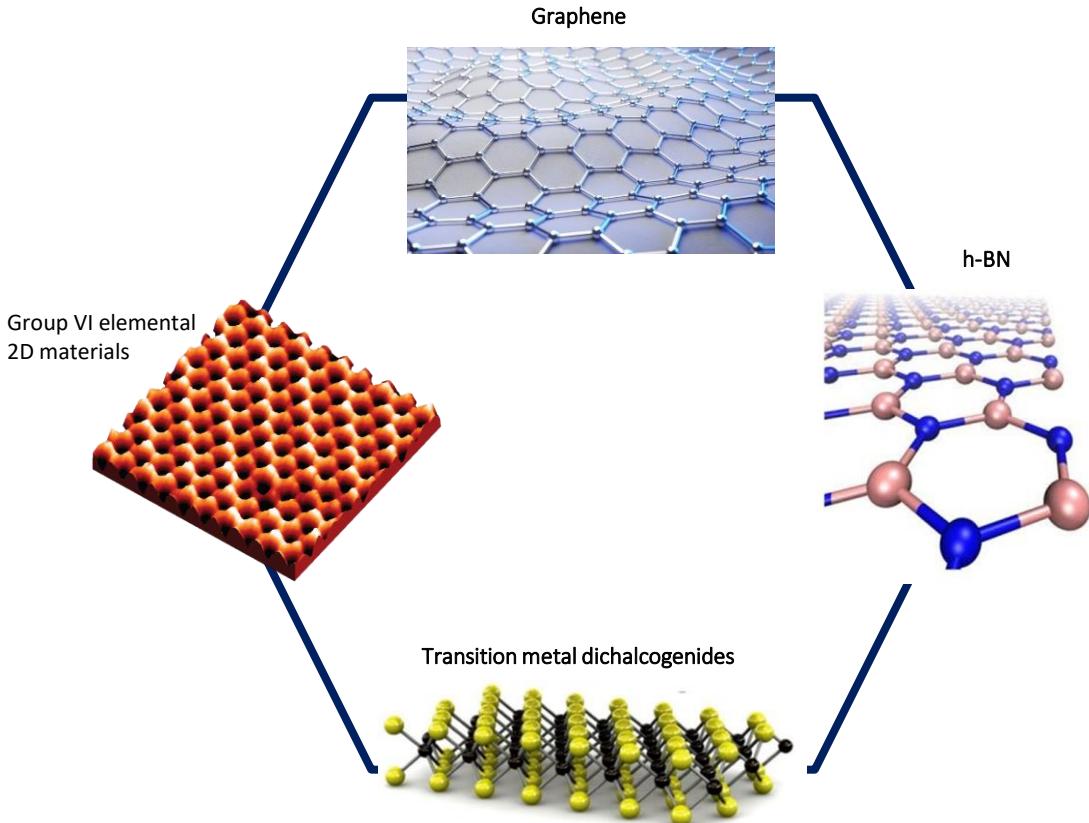
Pantelis Bampoulis

p.bampoulis@utwente.nl

Physics of Interfaces and Nanomaterials
(Chair: H. Zandvliet)

University of Twente, the Netherlands

2D materials

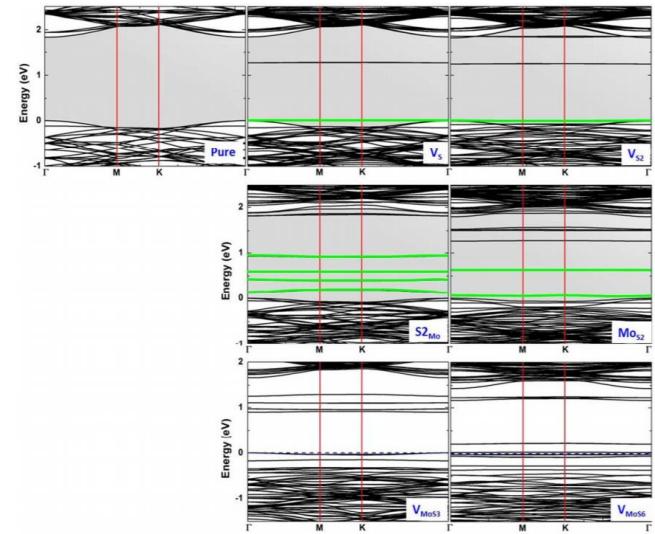
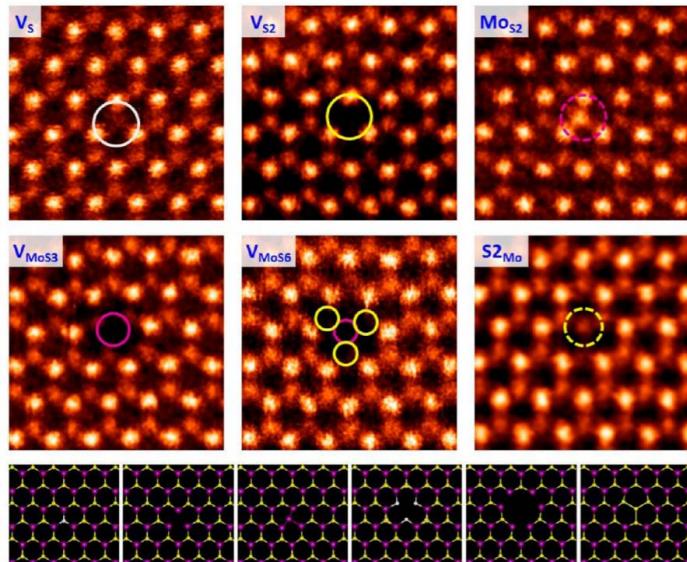


Modification of the Band-structure:

- ✓ Charge
- ✓ Strain
- ✓ Mixing
- ✓ Defects
- ✓ Stacking

2D materials

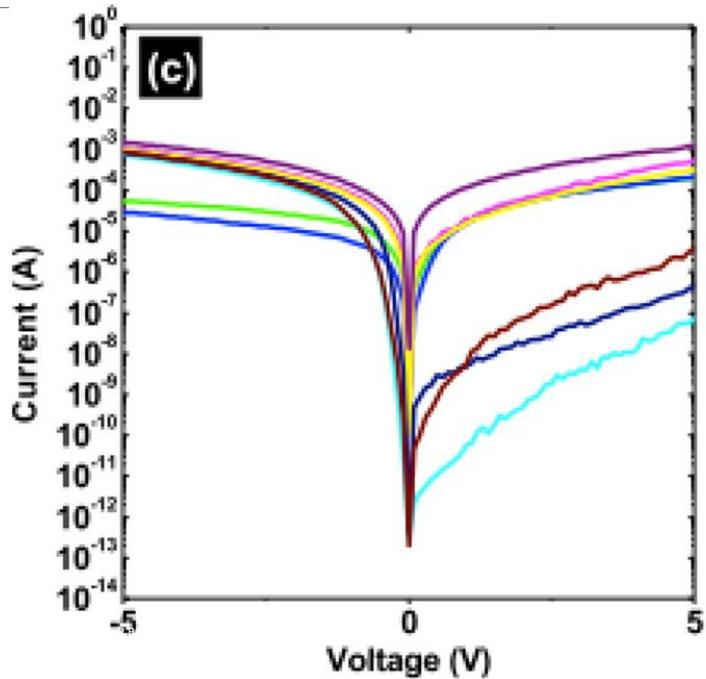
Defects in MoS₂



Nano Lett., 2013, 13 (6), pp 2615–2622

MoS₂-metal contacts

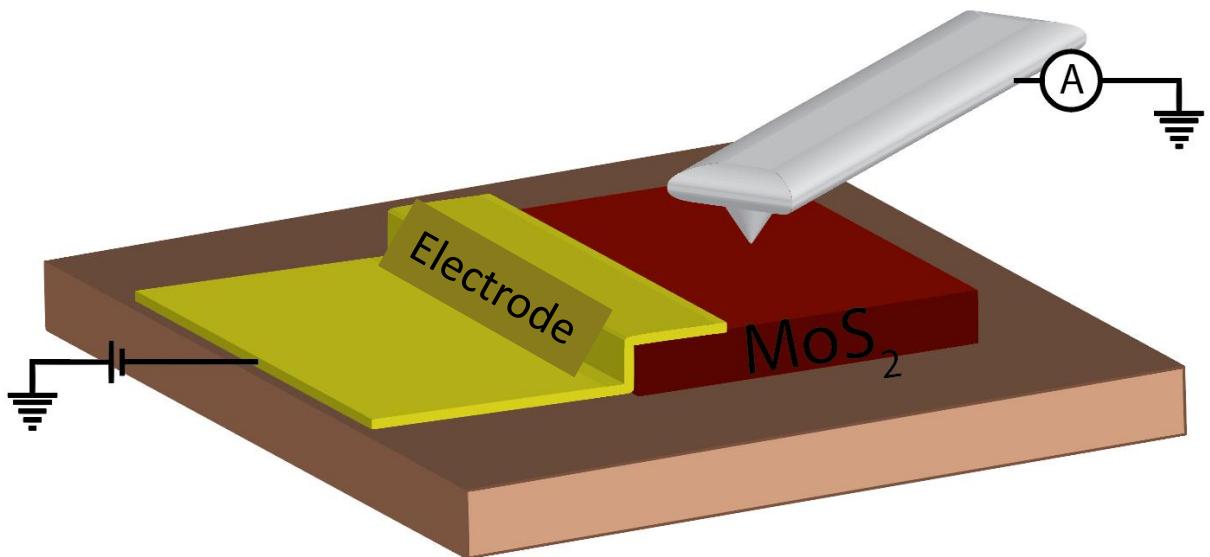
Unpredictable behavior



ACS Nano, 2014, 8 (3), 2880–2888

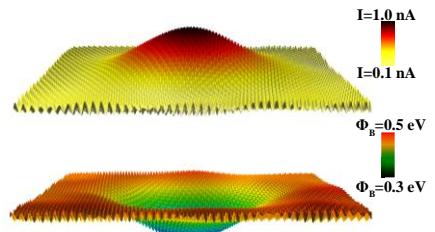
ACS Appl. Mater. Interfaces, 2015, 7 (22), 11921–11929

Conductive AFM as a nanoscopic tool for electrical characterization



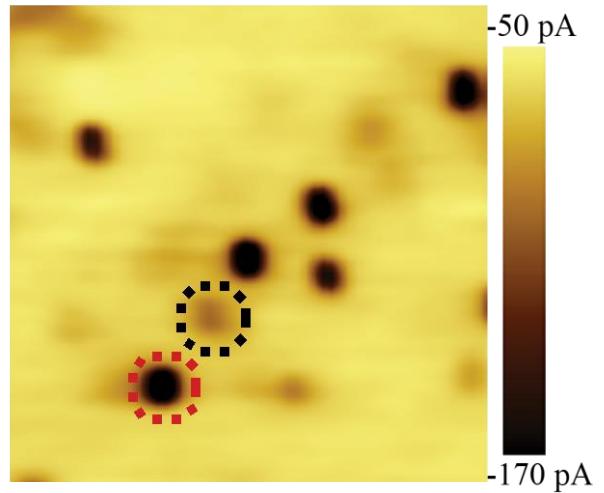
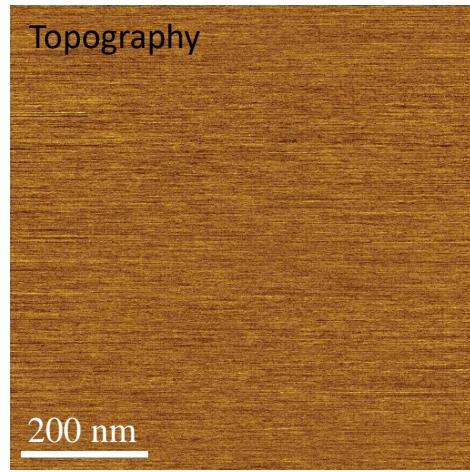
Overview

1. Schottky barrier heights in MoS₂/metal contacts

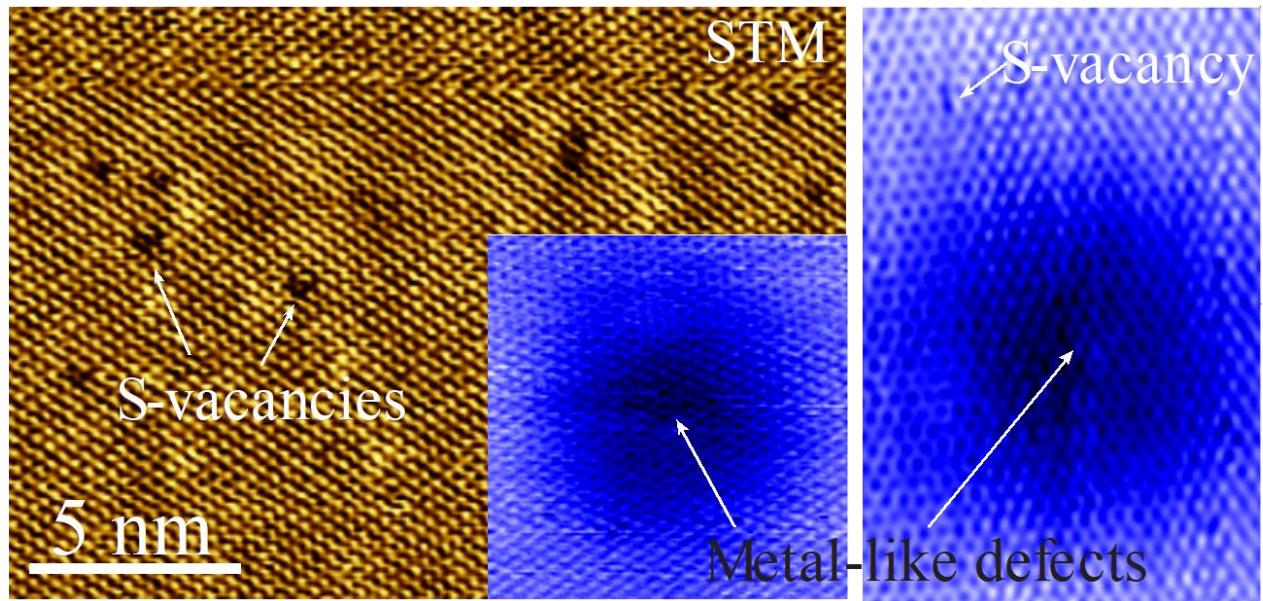


Schottky barrier heights in MoS₂/metal contacts

Visualization of Defects

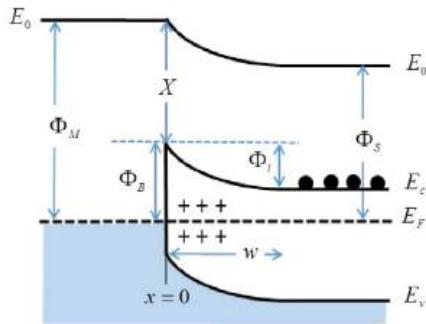
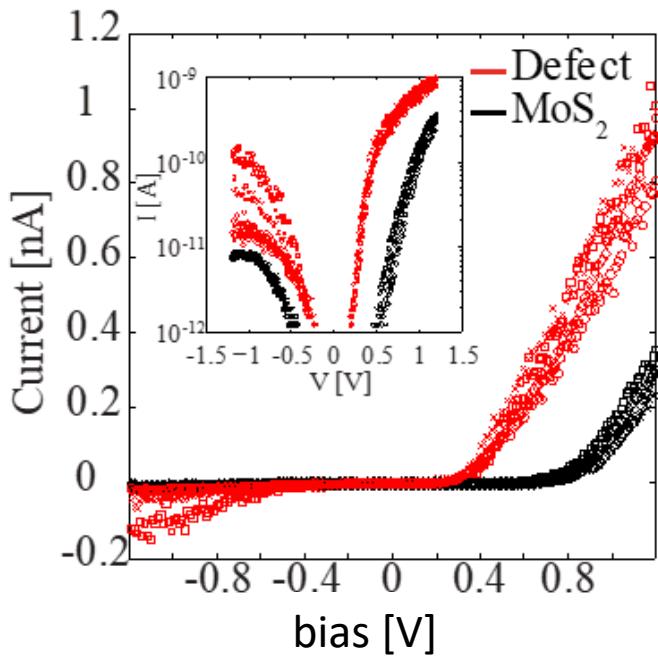


Defects located in the Mo-layer



Charge transport

Metal-Semiconductor contacts



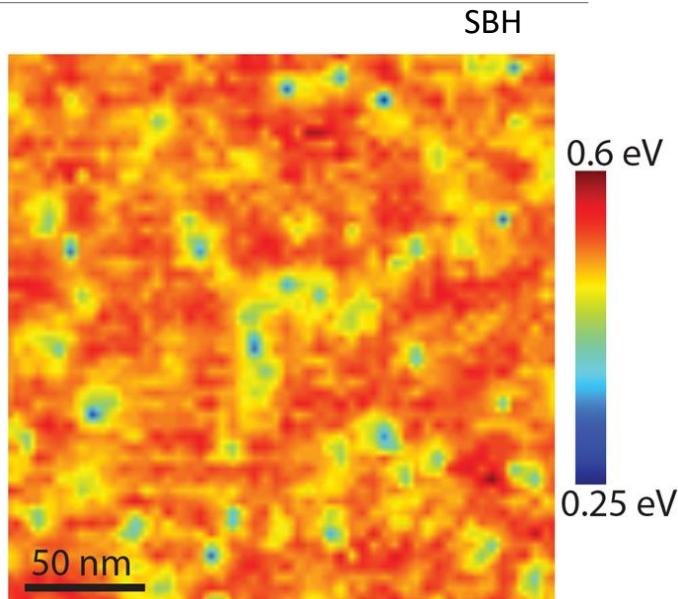
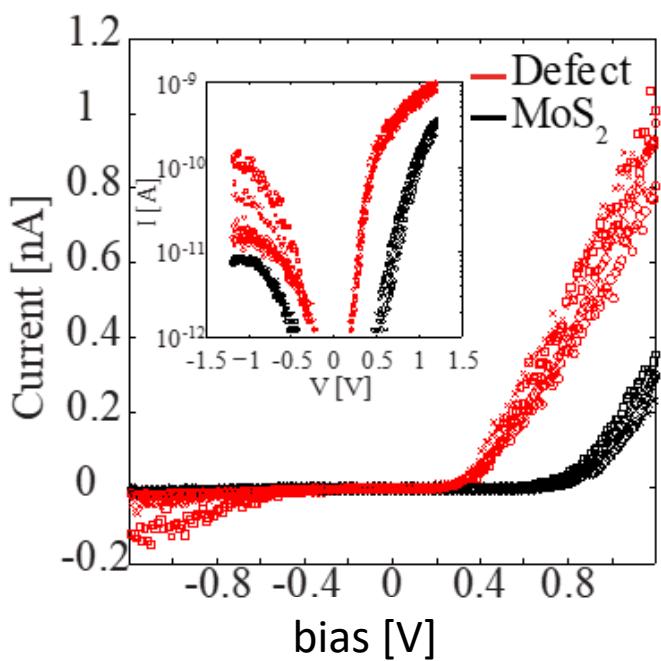
Thermionic emission:

$$I = I_0 \left[\exp\left(\frac{qV}{\eta k_B T}\right) - 1 \right] \quad \phi_B = \frac{k_B T}{q} \ln\left(\frac{A^* A T^2}{I_0}\right)$$

$$I_0 = A A^* T^2 \exp\left(-\frac{q\phi_B}{k_B T}\right)$$

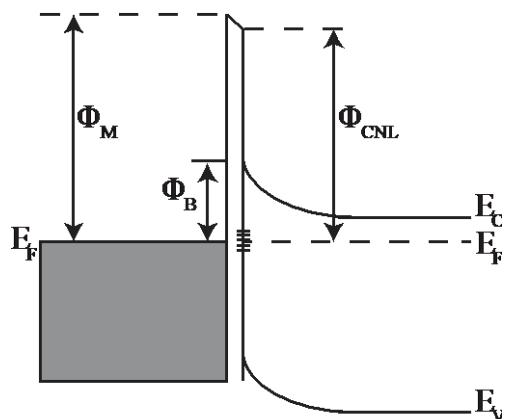
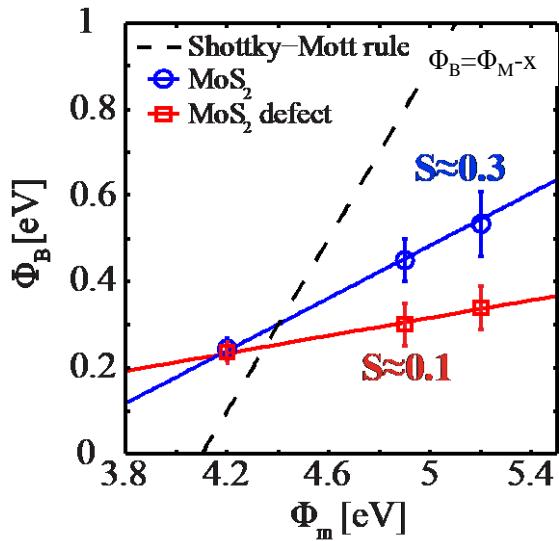
Charge transport

Metal-Semiconductor contacts



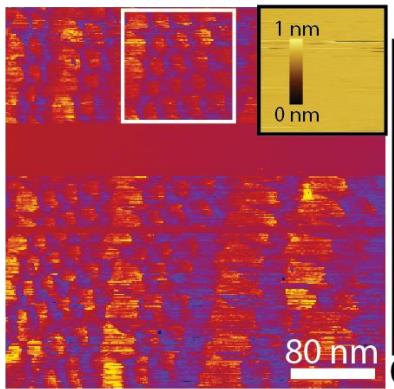
Charge transport

Fermi level pinning

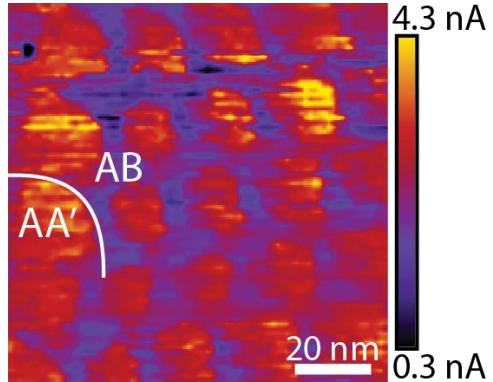


Bampoulis et al. , ACS Appl. Mater. Interfaces 9, 22, 19278-19286, 2017

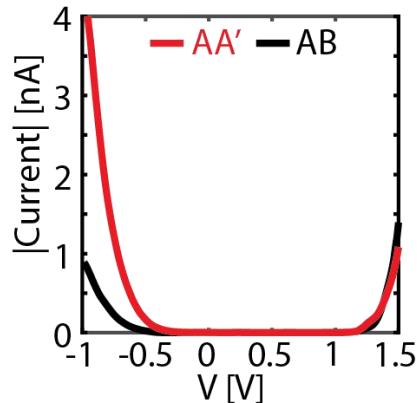
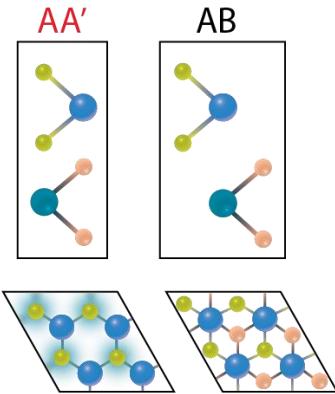
Stacking faults



5 nA
1 nm
0 nm
80 nm
0.1 nA



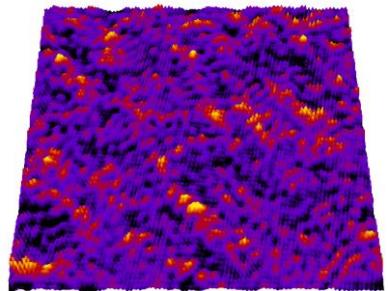
4.3 nA
20 nm
0.3 nA



4
3
2
1
0
AA'
AB
-1 -0.5 0 0.5 1 1.5
V [V]

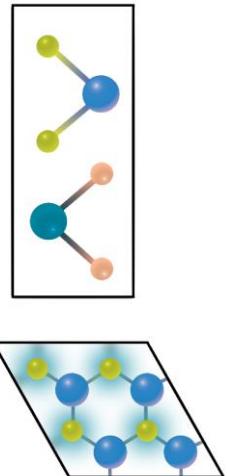
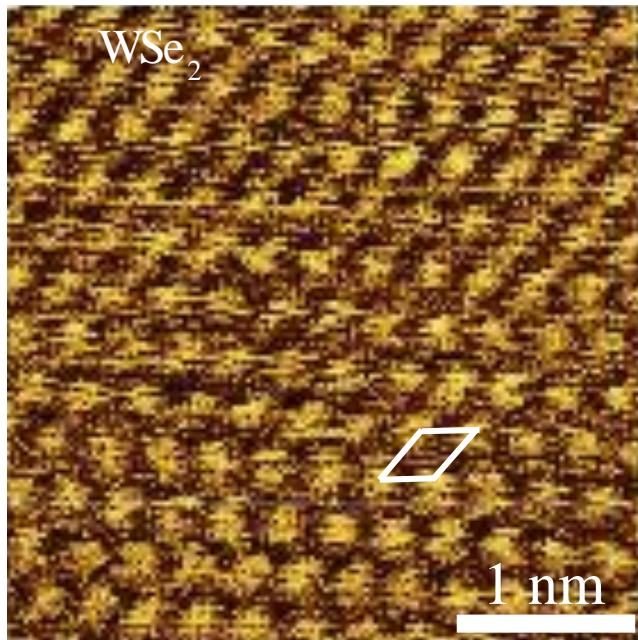
Overview

2. Local conduction in MoWSe₂ alloys



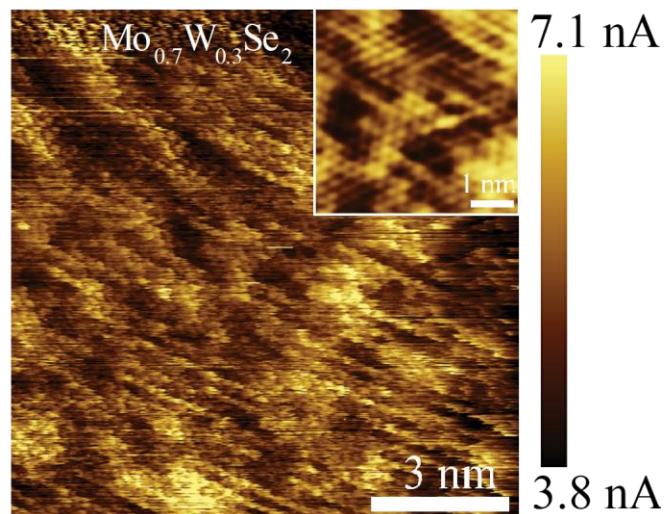
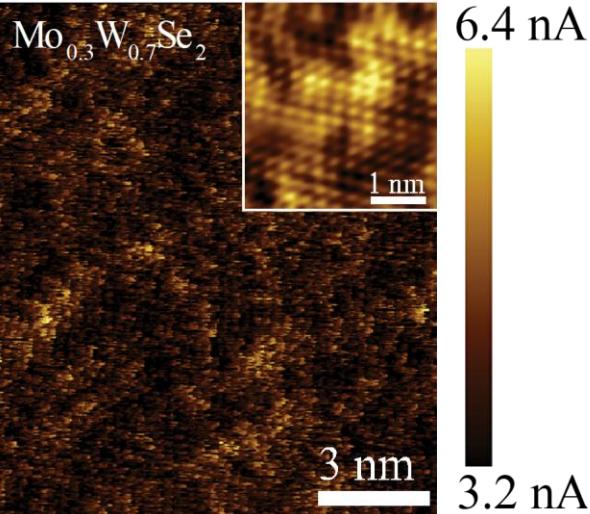
WSe₂

Atomic Periodicity with C-AFM



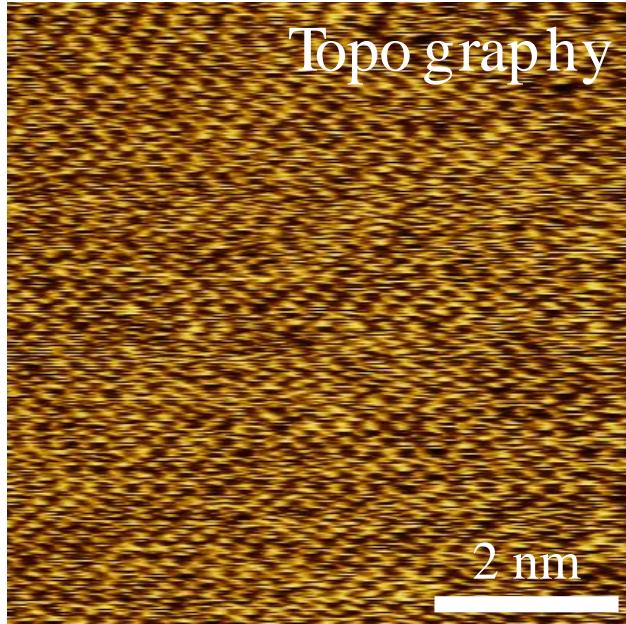
Local conduction in MoWSe₂ alloys

Segregation



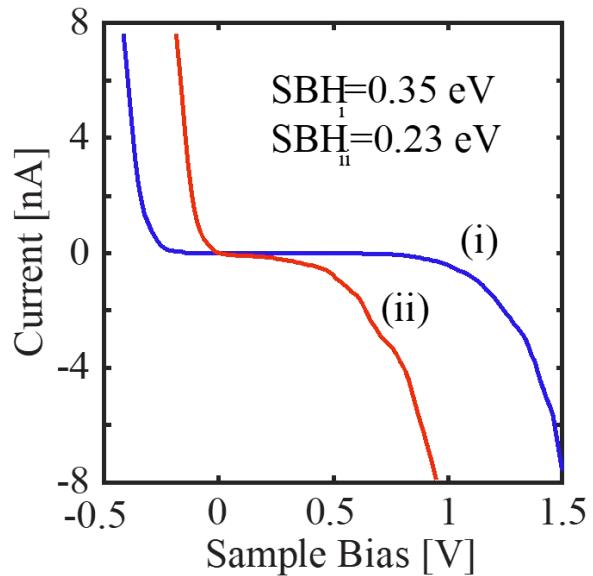
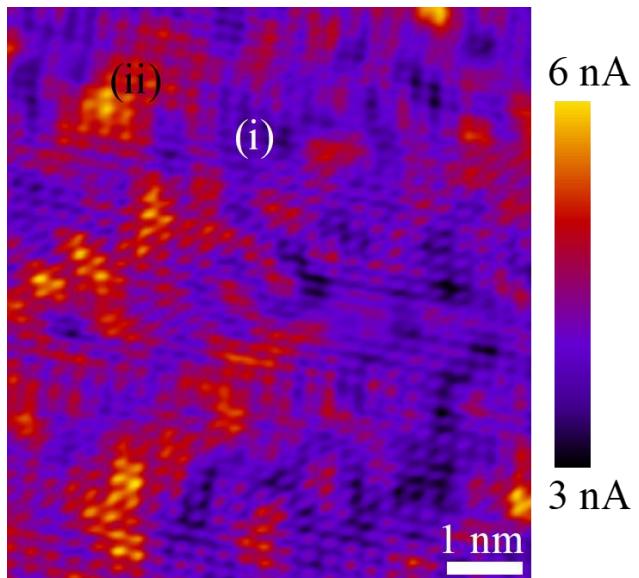
Local conduction in MoWSe₂ alloys

Segregation



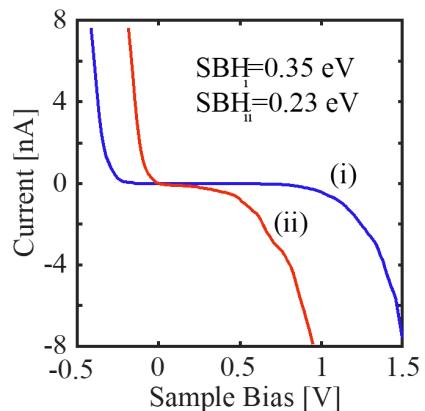
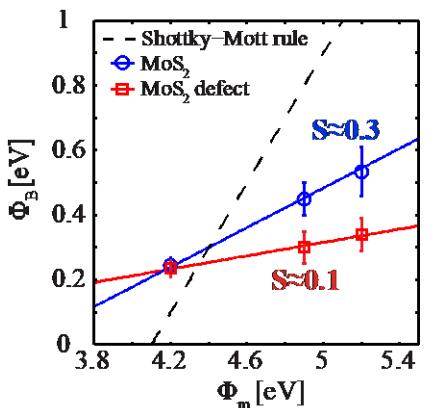
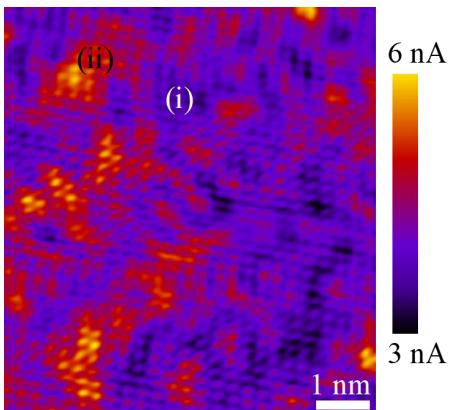
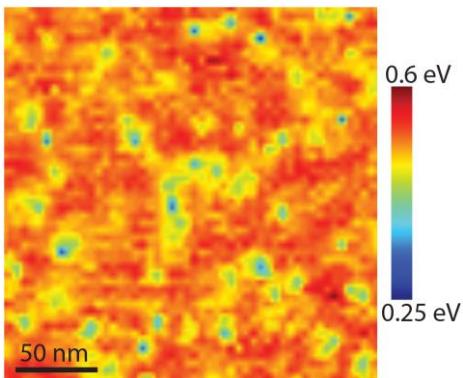
Local conduction in MoWSe₂ alloys

Segregation



Bampoulis et al., ACS Appl. Mater. Interfaces 10, 15, 13218-13225, 2018

Conclusions



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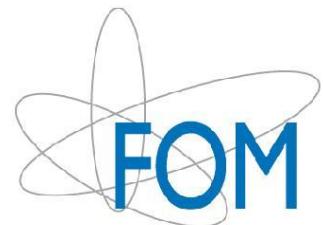
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Thank you for your attention